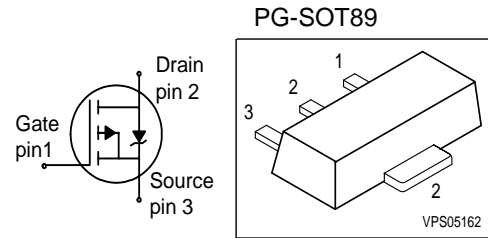


SIPMOS® Small-Signal-Transistor
Feature

- P-Channel
- Enhancement mode
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101


Product Summary

V_{DS}	-250	V
$R_{DS(on)}$	12	Ω
I_D	-0.19	A



Type	Package	Pb-free	Tape and Reel Information	Marking
BSS 192 P	PG-SOT89	Yes	L6327: 1000 pcs/reel	KC

Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	I_D	-0.19 -0.1	A
Pulsed drain current $T_A=25^\circ\text{C}$	$I_{D \text{ puls}}$	-0.76	
Reverse diode dv/dt $I_S=-0.19\text{A}$, $V_{DS}=-200\text{V}$, $di/dt=-200\text{A}/\mu\text{s}$, $T_{jmax}=150^\circ\text{C}$	dv/dt	6	$\text{kV}/\mu\text{s}$
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_A=25^\circ\text{C}$	P_{tot}	1	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JESD22-A114-HBM		Class 1a	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point (Pin 2)	R_{thJS}	-	-	10	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	125	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu\text{A}$	$V_{(BR)DSS}$	-250	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-130\mu\text{A}$	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current $V_{DS}=-250\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=-250\text{V}, V_{GS}=0, T_j=150^\circ\text{C}$	I_{DSS}	-	-0.1 -10	-0.2 -100	μA
Gate-source leakage current $V_{GS}=-20\text{V}, V_{DS}=0$	I_{GSS}	-	-10	-100	
Drain-source on-state resistance $V_{GS}=-2.8\text{V}, I_D=-0.025\text{A}$	$R_{DS(on)}$	-	10	20	Ω
Drain-source on-state resistance $V_{GS}=-4.5\text{V}, I_D=-0.1\text{A}$	$R_{DS(on)}$	-	8.3	15	
Drain-source on-state resistance $V_{GS}=-10\text{V}, I_D=-0.19\text{A}$	$R_{DS(on)}$	-	7.7	12	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$ V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = -0.1\text{A}$	0.19	0.38	-	S
Input capacitance	C_{iss}	$V_{GS} = 0, V_{DS} = -25\text{V}$, $f = 1\text{MHz}$	-	83	104	pF
Output capacitance	C_{oss}		-	13	16	
Reverse transfer capacitance	C_{rss}		-	6	8	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -125\text{V}, V_{GS} = -10\text{V}$, $I_D = -0.19\text{A}, R_G = 2\Omega$	-	4.7	7	ns
Rise time	t_r		-	5.2	8	
Turn-off delay time	$t_{d(off)}$		-	72	108	
Fall time	t_f		-	50	75	

Gate Charge Characteristics

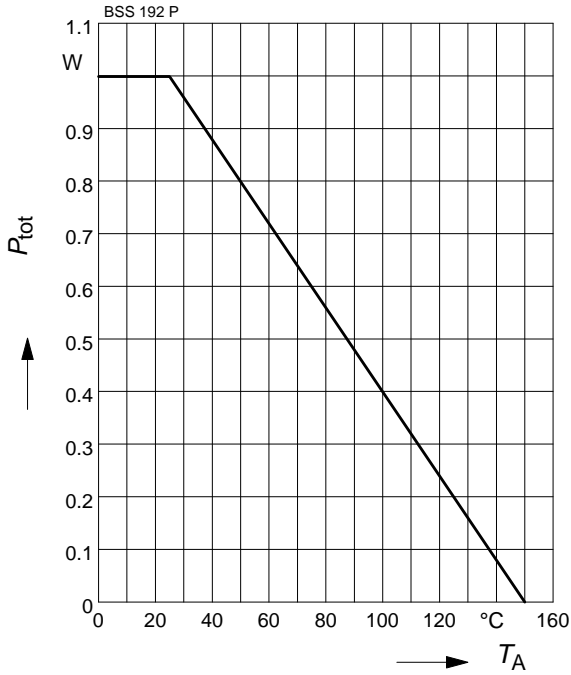
Gate to source charge	Q_{gs}	$V_{DD} = -200\text{V}, I_D = -0.19\text{A}$	-	-0.2	-0.25	nC
Gate to drain charge	Q_{gd}		-	-1.9	-2.4	
Gate charge total	Q_g	$V_{DD} = -200\text{V}, I_D = -0.19\text{A}$, $V_{GS} = 0 \text{ to } -10\text{V}$	-	-4.9	-6.1	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -200\text{V}, I_D = -0.19\text{A}$	-	-2.63	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25\text{ }^\circ\text{C}$	-	-	-0.19	A
Inv. diode direct current, pulsed	I_{SM}		-	-	-0.76	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0, I_F = -0.19\text{A}$	-	-0.78	-1.1	V
Reverse recovery time	t_{rr}	$V_R = -125\text{V}, I_F = I_S$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	46	57	ns
Reverse recovery charge	Q_{rr}		-	72	90	

1 Power dissipation

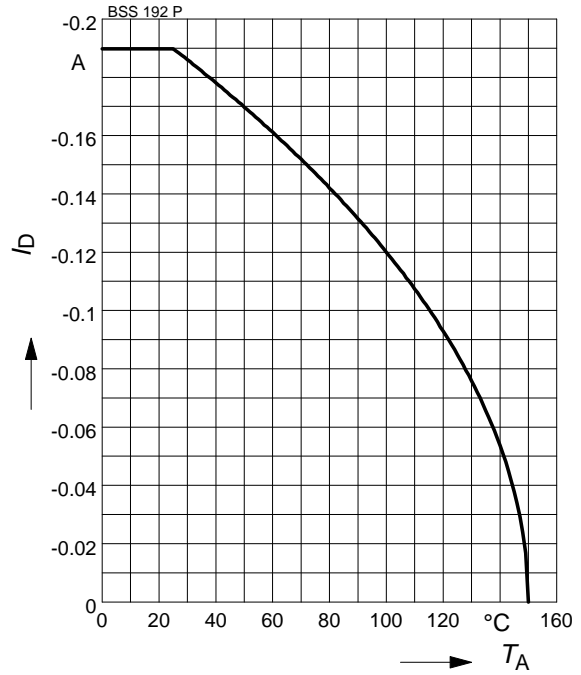
$$P_{\text{tot}} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

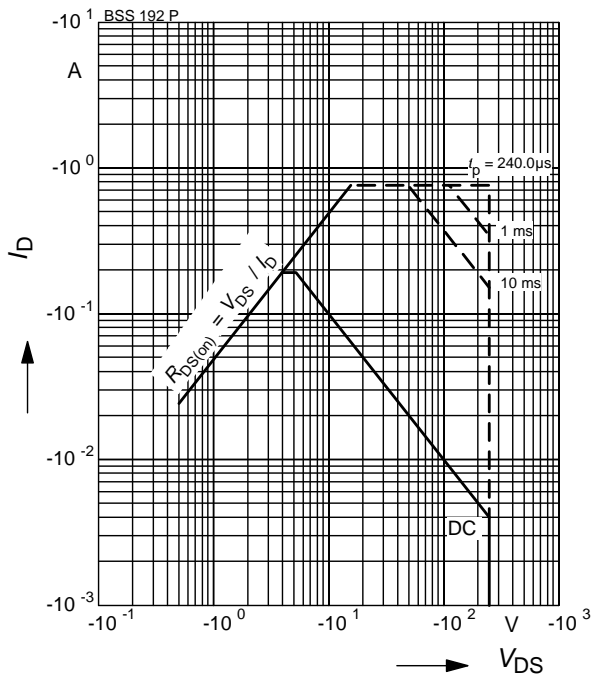
parameter: $|V_{GS}| \geq 10V$



3 Safe operating area

$$I_D = f(V_{DS})$$

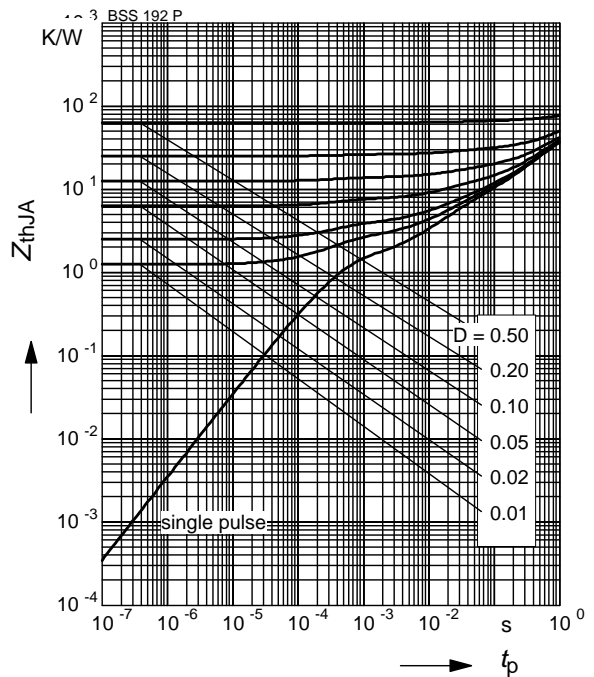
parameter: $D = 0, T_A = 25^\circ C$



4 Transient thermal impedance

$$Z_{\text{thJA}} = f(t_p)$$

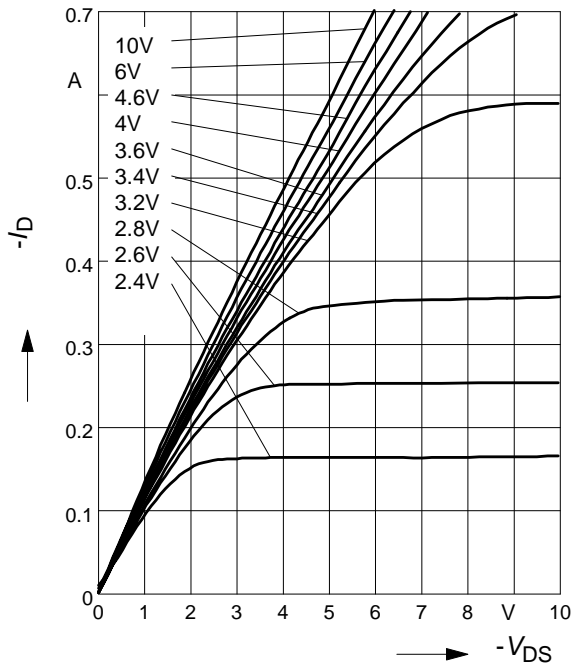
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS})$

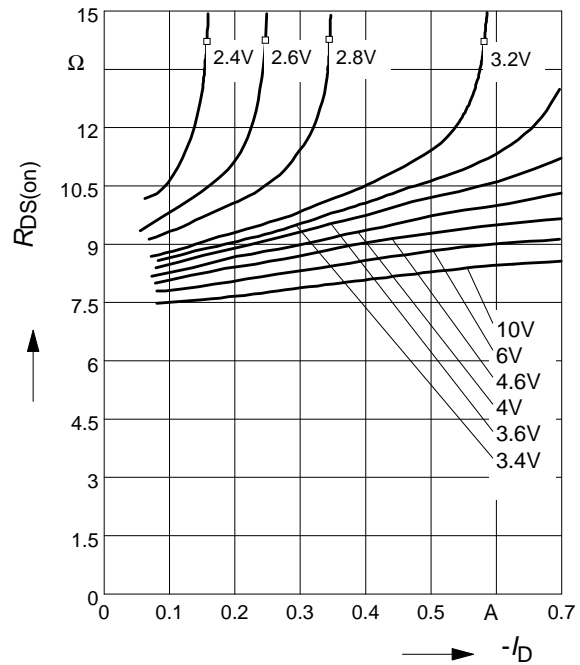
parameter: $T_j = 25^\circ\text{C}$, $-V_{GS}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

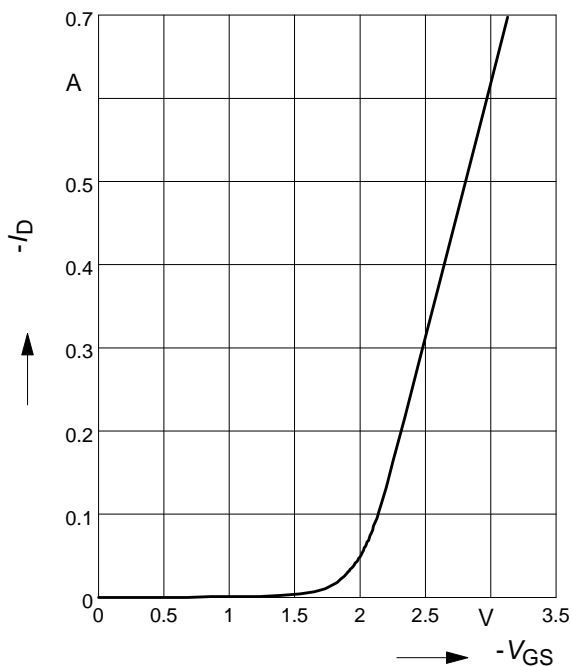
parameter: V_{GS} ; $T_j = 25^\circ\text{C}$, $-V_{GS}$



7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $|V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

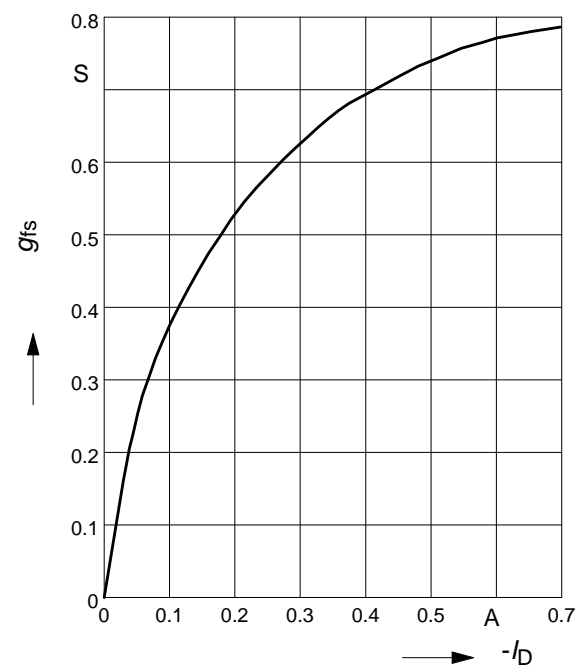
parameter: $T_j = 25^\circ\text{C}$



8 Typ. forward transconductance

$g_{fs} = f(I_D)$

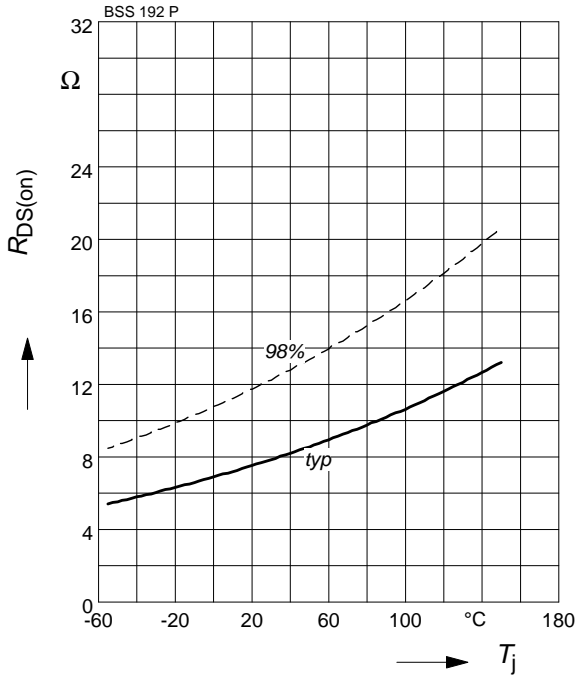
parameter: $T_j = 25^\circ\text{C}$



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

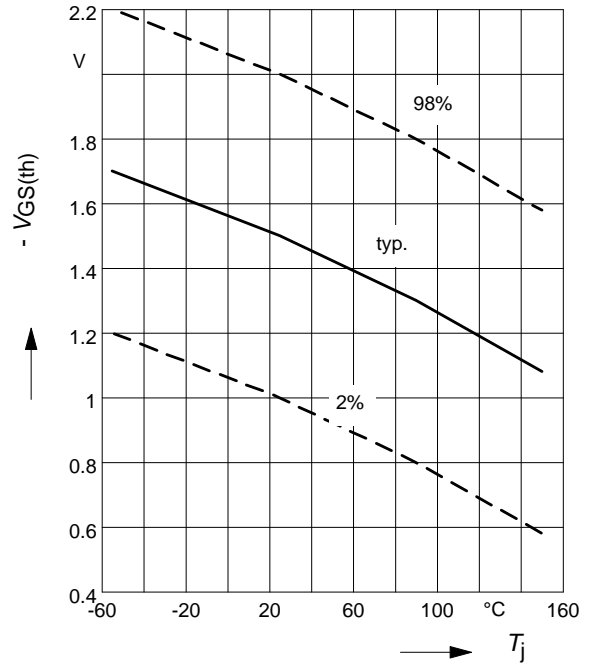
parameter: $I_D = -0.19 \text{ A}$, $V_{GS} = -10 \text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

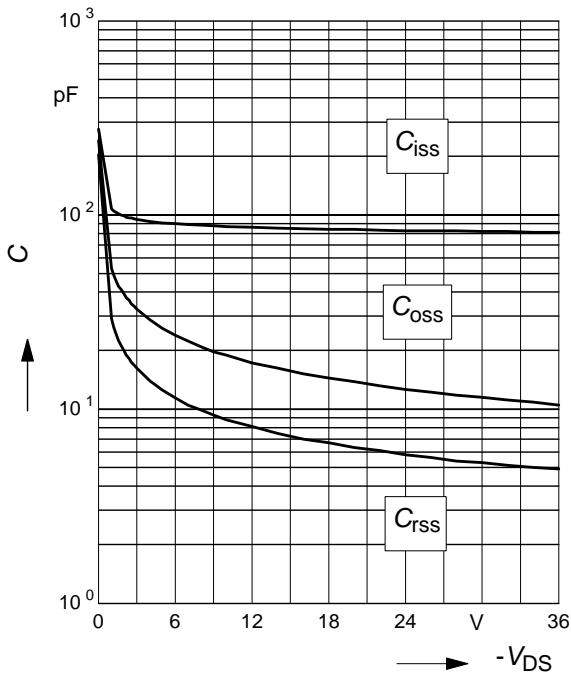
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

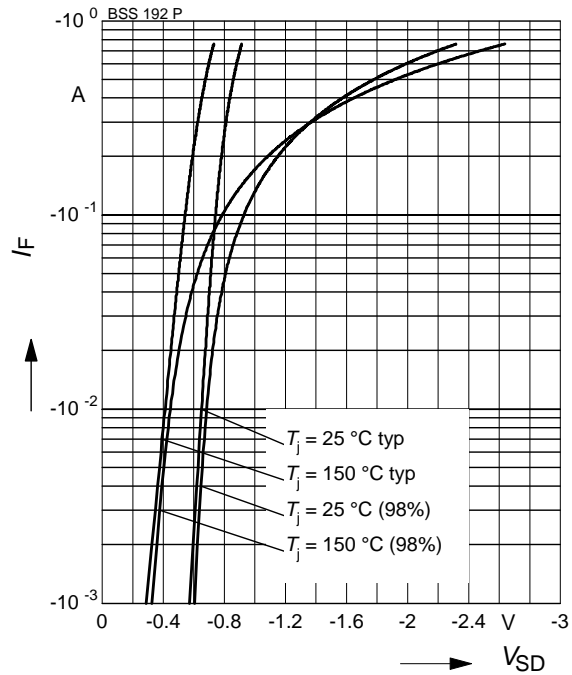
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$, $T_j = 25 \text{ }^\circ\text{C}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

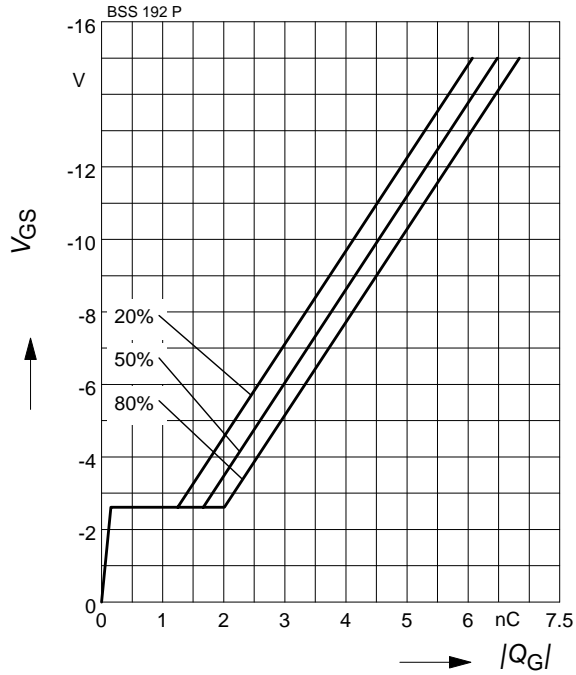
parameter: T_j



13 Typ. gate charge

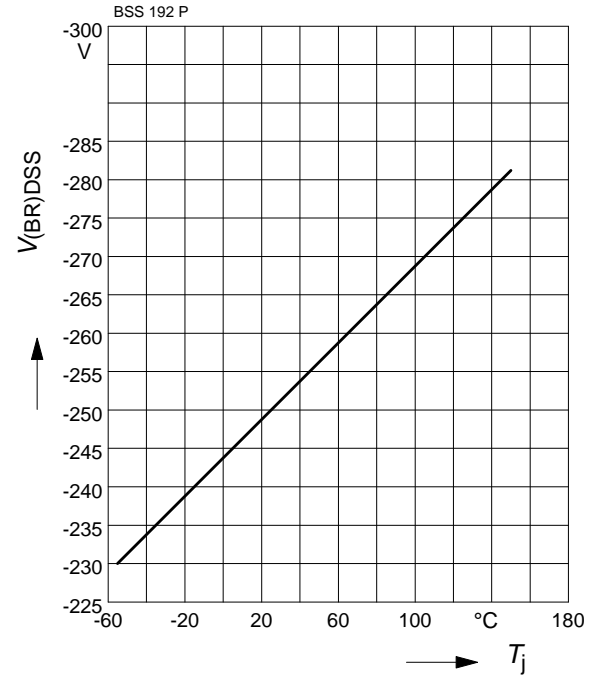
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = -0.19$ A pulsed, $T_j = 25$ °C



14 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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